

## Silicon N-Channel Power MOSFET

### General Description:

HME6N150, the silicon N-channel Enhanced VDMOSFET, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-3PH, which accords with the RoHS standard.

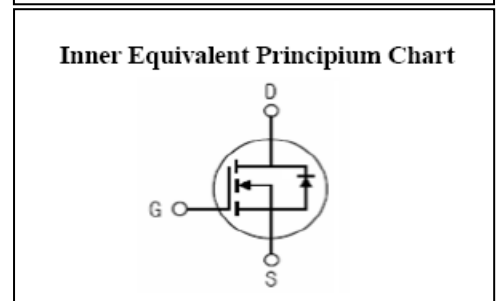
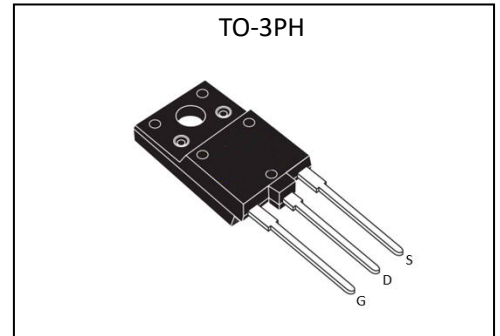
$V_{DSS}$	1500	V
$I_D$	6	A
$P_D(T_C=25^\circ\text{C})$	70	W
$R_{DS(ON)TYPE}$	2.5	$\Omega$

### Features:

- Fast Switching
- Low ON Resistance
- Low Gate Charge Minimize Switching loss
- Fast Recovery Body Diode
- 100% Single Pulse avalanche energy Test

### Applications:

- Adaptor
- Charger
- SMPS Standby Power



### Absolute ( $T_C=25^\circ\text{C}$ unless otherwise specified):

Symbol	Parameter	Rating	Units
$V_{DSS}$	Drain-to-Source Voltage	1500	V
$I_D$	Continuous Drain Current	6	A
$I_{DM}$	Pulsed Drain Current at $V_{GS}=10V$	24	A
$V_{GS}$	Gate-to-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulse Avalanche Energy	200	mJ
dv/dt	Peak Diode Recovery dv/dt	5.0	V/ns
$P_D$	Power Dissipation	70	W
	Derating Factor above $25^\circ\text{C}$	0.56	W/ $^\circ\text{C}$
$T_J, T_{stg}$	Operating Junction and Storage Temperature Range	150, -55 to 150	$^\circ\text{C}$
$T_L$	Maximum Temperature for Soldering	300	$^\circ\text{C}$
$T_{PAK}$	Leads at 0.63 in(1.6mm) from Case for 10 seconds, Package Body for 10 seconds	260	$^\circ\text{C}$

Caution Stresses greater than those in the "Absolute Maximum Ratings" may cause permanent damage to the device

## Thermal Characteristics

Symbol	Parameter	Rating	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.78	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	40	$^{\circ}\text{C}/\text{W}$

## Electrical Characteristics (Tc= 25°C unless otherwise specified) :

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$V_{DSS}$	Drain to Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	1500	--	--	V
$I_{DSS}$	Drain to Source Leakage Current	$V_{DS}=1500\text{V}, V_{GS}=0\text{V}, T_a=25^{\circ}\text{C}$	--	--	10	$\mu\text{A}$
		$V_{DS}=1200\text{V}, V_{GS}=0\text{V}, T_a=125^{\circ}\text{C}$	--	--	250	
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+30\text{V}$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-30\text{V}$	--	--	-100	nA

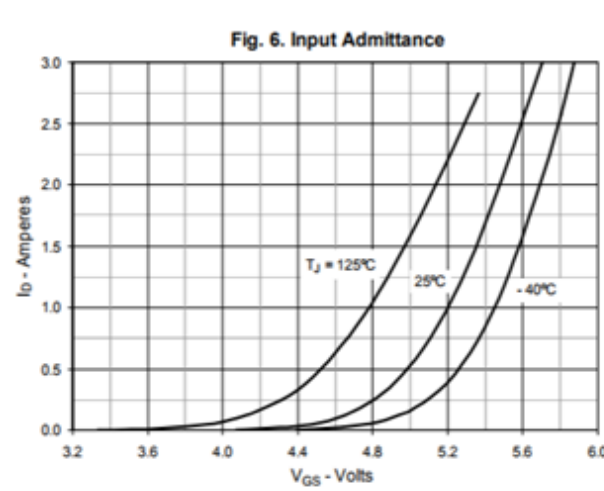
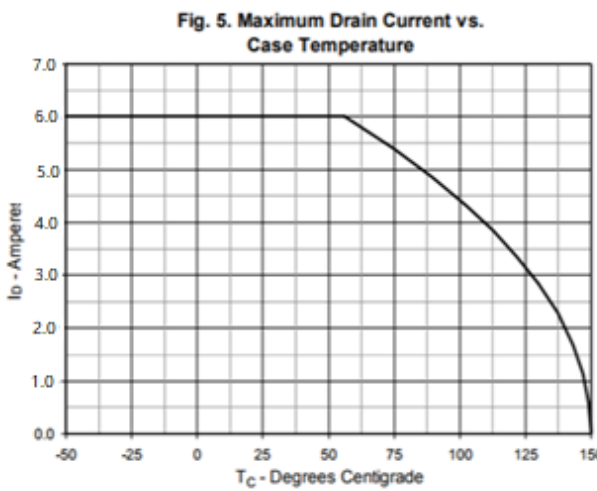
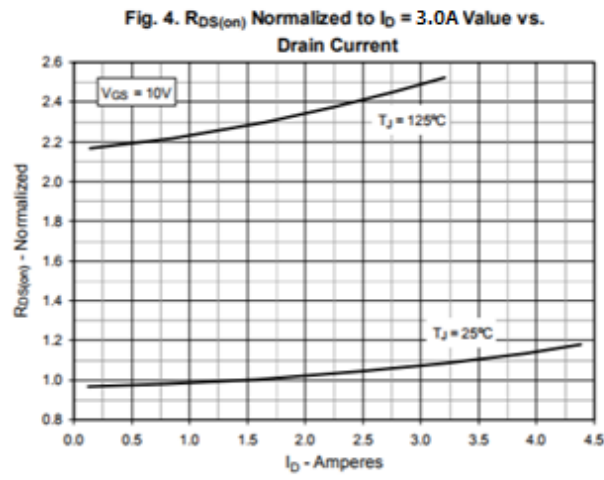
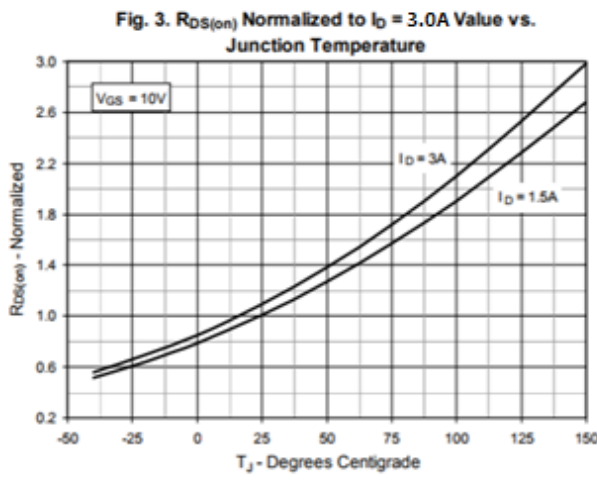
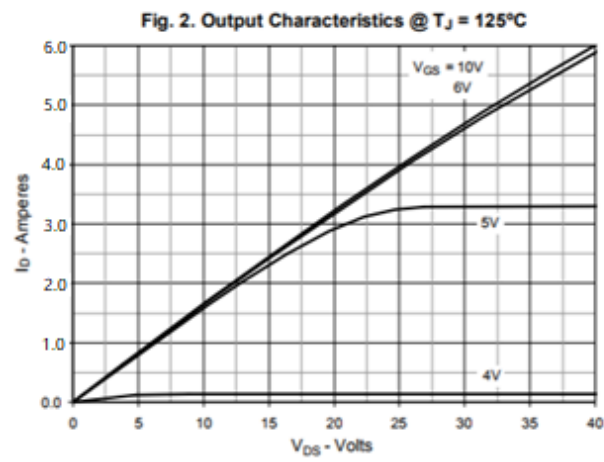
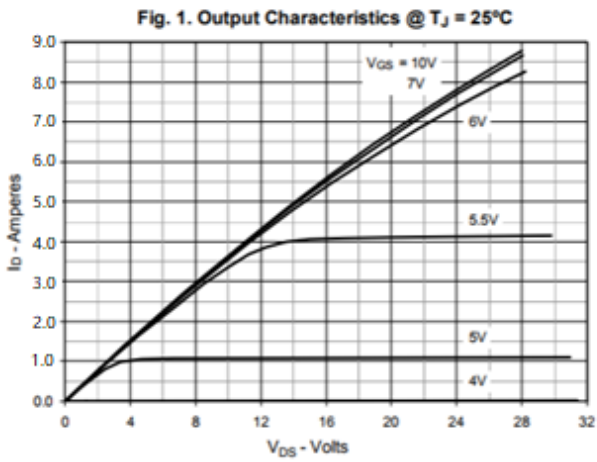
ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10\text{V}, I_D=3.0\text{A}$	--	2.5	3.5	$\Omega$
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2.5	--	4.5	V
$g_{fs}$	Forward Transconductance	$V_{DS}=15\text{V}, I_D=3\text{A}$	--	2.0	--	S

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=25\text{V}$ $f=1.0\text{MHz}$	--	3800	--	pF
$C_{oss}$	Output Capacitance		--	200	--	
$C_{rss}$	Reverse Transfer Capacitance		--	26	--	

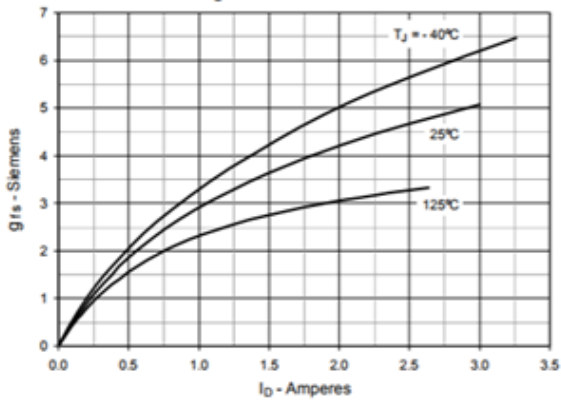
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=3\text{A}, V_{DD}=750\text{V}$ $V_{GS}=10\text{V}, R_g=10\Omega$	--	45	--	ns
$t_r$	Rise Time		--	20	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	70	--	
$t_f$	Fall Time		--	35	--	
$Q_g$	Total Gate Charge	$I_D=3\text{A}, V_{DD}=750\text{V}$ $V_{GS}=10\text{V}$	--	19	--	nC
$Q_{gs}$	Gate to Source Charge		--	30	--	
$Q_{gd}$	Gate to Drain ( "Miller" ) Charge		--	11	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$I_{SD}$	Continuous Source Current (Body Diode)		--	--	6	A
$I_{SM}$	Maximum Pulsed Current (Body Diode)		--	--	24	A
$V_{SD}$	Diode Forward Voltage	$I_S=6A, V_{GS}=0V$	--	--	5	V
$t_{rr}$	Reverse Recovery Time	$I_S=6A, T_j=25^\circ C$	--	300	--	ns
$Q_{rr}$	Reverse Recovery Charge	$di/dt=100A/\mu s, V_{GS}=0V$	--		--	nC
*Pulse width $t_p \leq 380\mu s, \delta \leq 2\%$						

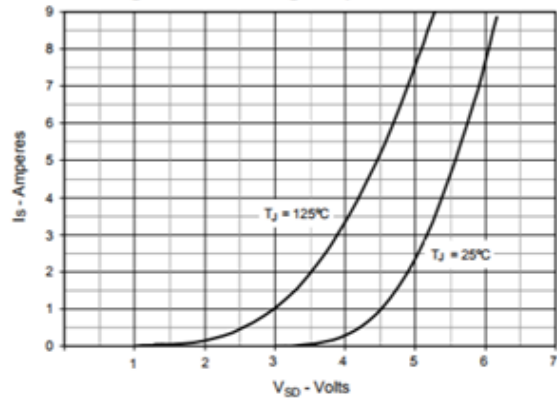
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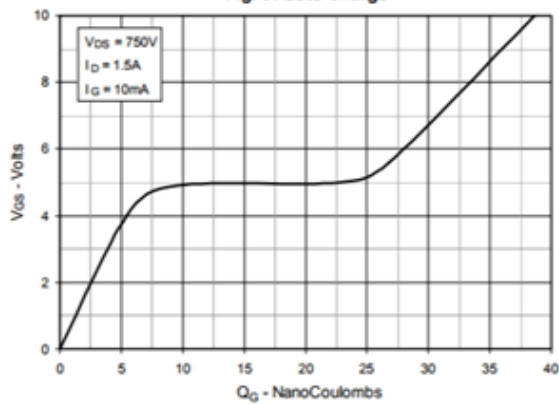
**Fig. 7. Transconductance**



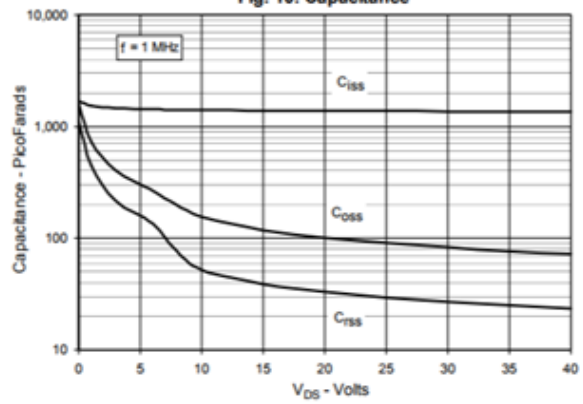
**Fig. 8. Forward Voltage Drop of Intrinsic Diode**



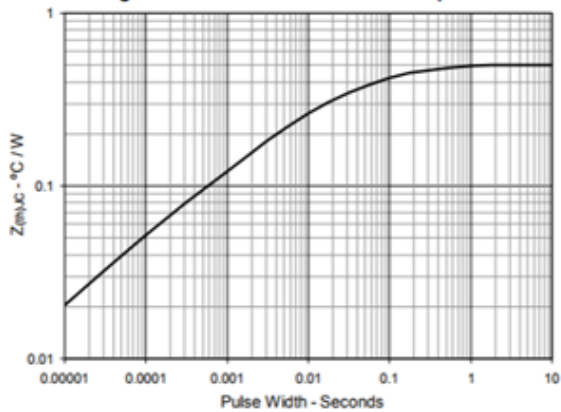
**Fig. 9. Gate Charge**



**Fig. 10. Capacitance**



**Fig. 11. Maximum Transient Thermal Impedance**



**Fig. 12. Forward-Bias Safe Operating Area**

